Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

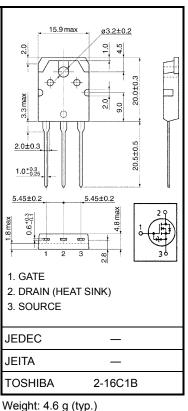
2SK2550

Chopper Regulator, DC–DC Converter and Motor Drive Applications

- Low drain-source ON resistance $: RDS(ON) = 24 \text{ m}\Omega(typ.)$
- High forward transfer admittance $: |Y_{fs}| = 27 \text{ S (typ.)}$
- Low leakage current $: I_{DSS} = 100 \ \mu A \ (max) \ (V_{DS} = 50 \ V)$
- Enhancement mode : $V_{th} = 1.5 \sim 3.5 \text{ V} (V_{DS} = 10 \text{ V}, \text{ ID} = 1 \text{ mA})$

JSolute Maximum Ratings (1a – 25 C)							
Characteristics		Symbol	Rating	Unit			
Drain-source voltage		V _{DSS}	50	V			
Drain-gate voltage (R _{GS} = 20 kΩ)		V _{DGR}	50	V			
Gate-source voltage		V _{GSS}	±20	V			
Drain current	DC (Note 1)	Ι _D	45	Α			
	Pulse (Note 1)	I _{DP}	135	Α			
Drain power dissipation	n (Tc = 25°C)	PD	100	W			
Single pulse avalanche energy (Note 2)		E _{AS}	115	mJ			
Avalanche current		I _{AR}	45	Α			
Repetitive avalanche energy (Note 3)		E _{AR}	10	mJ			
Channel temperature		T _{ch}	150	°C			
Storage temperature range		T _{stg}	-55~150	°C			

Absolute Maximum Ratings (Ta = 25°C)



Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	1.25	°C / W
Thermal resistance, channel to ambient	R _{th (ch−a)}	50	°C / W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 25 V, T_{ch} = 25°C (initial), L = 71 µH, R_G = 25 Ω , I_{AR} = 45 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.

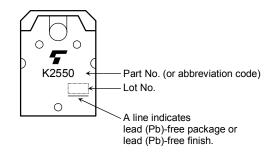
Electrical Characteristics (Ta = 25°C)

Charao	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	urrent	I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V		_	±10	μA
Drain cut-off cu			V _{DS} = 50 V, V _{GS} = 0 V	_	_	100	μA
Drain-source br	reakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	50	_	_	V
Gate threshold	voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	1.5	_	3.5	V
Drain-source O	N resistance	R _{DS (ON)}	V _{GS} = 10 V, I _D = 25 A		24	30	mΩ
Forward transfe	r admittance	Y _{fs}	V _{DS} = 10 V, I _D = 25 A	15	27		S
Input capacitance	ce	C _{iss}			1250		
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		250		pF
Output capacitance		Coss			700		
Switching time	Rise time	tr	$V_{GS} \stackrel{10 \text{ V}}{_{0 \text{ V}}} \prod_{\substack{I_D = 25 \text{ A} \\ \bigcirc \text{V}_{out}}} V_{out}$ $R_L = 1.2 \Omega$ $V_{DD} = 30 \text{ V}$	_	20	_	ns
	Turn-on time	t _{on}		_	30	_	
	Fall time	t _f		_	40	_	
	Turn-off time	t _{off}	Duty $\leq 1\%$, t _w = 10 µs	_	120	_	
Total gate charge (Gate-source plus gate-drain)		Qg			36	_	
Gate-source charge		Q _{gs}	V _{DD} ≈ 40 V, V _{GS} = 10 V, I _D = 45 A		22	_	nC
Gate-drain ("miller") charge		Q _{gd}			14	_	

Source–Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	—	_	_	45	А
Pulse drain reverse current (Note 1)	I _{DRP}	—	_	_	135	A
Forward voltage (diode)	V _{DSF}	I _{DR} = 45 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	trr	I _{DR} = 45 A, V _{GS} = 0 V dI _{DR} / dt = 50 A / μs	_	75	_	ns
Reverse recovered charge	Q _{rr}	dI _{DR} / dt = 50 A / μs	_	75	_	nC

Marking



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